



# Bipolar PNP Bare Die – BTP036T

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## Part Description

The BTP036T is a silicon BJT transistor available in bare die form and well suited for use in High Voltage Driver applications.

## Key Parameters:

- VCBO = -600V
- VCEO = -600V
- VEBO = -7V
- hFE = 95-410 @ VCE = -5V, IC = -0.05A
- VCE(Sat) = -1.05V @ IC = -0.1A, IB = -10mA
- fT = 30 MHz @ VCE = -10V, IE = 0A
- COBO = 40pF @ VCB = -10V

## Features

Designed to provide performance equivalent to TOSHIBA 2SA2142

## Die Size (Unawn)

1940 $\mu$ m X 1940 $\mu$ m, 76 Mils X 76 Mils

This is a shortform datasheet only

For the full datasheet

Please contact [sales@siliconsupplies.com](mailto:sales@siliconsupplies.com)

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